# **SG6612WN**

# 650V 50A Insulated Gate Bipolar Transistor

Datasheet

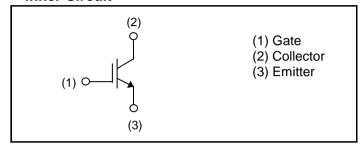
| $V_{CES}$                     | 650V    |
|-------------------------------|---------|
| I <sub>C (Nominal)</sub>      | 50A     |
| V <sub>CE(sat) (Typ.)</sub>   | 1.65V   |
| Max. Possible Chips per Wafer | 1272pcs |

# ●Outline Wafer (W05) Unsawn on foil (U03)

### Features

- 1) Trench Light Punch Through Type
- 2) Low Collector Emitter Saturation Voltage
- 3) Low Switching Loss
- 4) Short Circuit Withstand Time 5µs

## ●Inner Circuit



# Application

General Inverter

**UPS** 

**Power Conditioner** 

Welding

Absolute Maximum Ratings

| - 7 the definite maximum 1 taming                  |                              |             |      |  |  |
|--|------------------------------|-------------|------|--|--|
| Parameter  | Symbol                       | Value       | Unit |  |  |
| Collector - Emitter Voltage, T <sub>j</sub> = 25°C | V <sub>CES</sub>             | 650         | V    |  |  |
| Gate - Emitter Voltage                             | $V_{GES}$                    | ±30         | V    |  |  |
| Collector Current                                  | I <sub>C</sub> <sup>*1</sup> | *1)         | А    |  |  |
| Pulsed Collector Current                           | I <sub>CP</sub> *2           | 150         | А    |  |  |
| Operating Junction Temperature                     | T <sub>j</sub>               | -40 to +175 | °C   |  |  |

<sup>\*1</sup> Depending on thermal properties of assembly

<sup>\*2</sup> Pulse width limited by  $T_{\text{jmax}}$ .

# ●Design Assurance

| Parameter                        | Symbol Conditions  |  | Values      |      |      | Unit  |
|----------------------------------|--------------------|--|-------------|------|------|-------|
| raiailletei                      | Symbol             | Conditions   | Min.        | Тур. | Max. | Offic |
|                                  |                    | $V_{CC} \le 360V$ ,  |             |      |      |       |
| Short Circuit Withstand Time     | t <sub>sc</sub> *3 | $V_{CC} \le 360V$ ,<br>$V_{GE} = 15V$ ,<br>$T_i = 25^{\circ}C$   | 5           | -    | -    | μs    |
|                                  |                    | T <sub>j</sub> = 25°C  |             |      |      |       |
|                                  |                    | $I_C = 150A, V_{CC} = 520V,$   |             |      |      |       |
| Reverse Bias Safe Operating Area | RBSOA*3            | $I_C = 150A$ , $V_{CC} = 520V$ , $V_P = 650V$ , $V_{GE} = 15V$ , $R_G = 50\Omega$ , $T_j = 175^{\circ}C$ | FULL SQUARE |      | -    |       |
|                                  |                    | $R_G = 50\Omega, T_j = 175^{\circ}C$   |             |      |      |       |

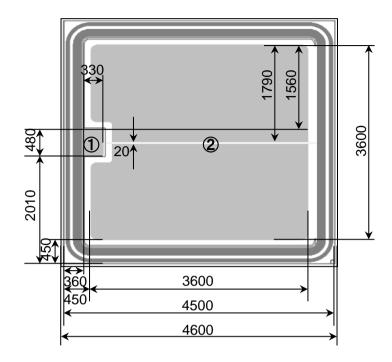
<sup>\*3</sup> Design assurance without measurement

# ● Electrical Characteristics (at T<sub>i</sub> = 25°C unless otherwise specified, in case of TO-247N package)

| Doromator Symbol Conditions               |                               | Values  |      |             | l locit |      |
|---|-------------------------------|---|------|-------------|---------|------|
| Parameter                                 | Parameter Symbol Conditions - |   | Min. | Тур.        | Max.    | Unit |
| Collector - Emitter Breakdown<br>Voltage  | BV <sub>CES</sub>             | $I_{C} = 10 \mu A, V_{GE} = 0 V$                                  | 650  | 1           | -       | ٧    |
| Collector Cut - off Current               | I <sub>CES</sub>              | $V_{CE} = 650V, V_{GE} = 0V$                                      | -    | -           | 10      | μΑ   |
| Gate - Emitter Leakage<br>Current         | I <sub>GES</sub>              | $V_{GE} = \pm 30V, V_{CE} = 0V$                                   | -    | -           | ±200    | nA   |
| Gate - Emitter Threshold<br>Voltage       | $V_{GE(th)}$                  | $V_{CE} = 5V, I_{C} = 34.7 \text{mA}$                             | 5.0  | 6.0         | 7.0     | V    |
| Collector - Emitter Saturation<br>Voltage | V <sub>CE(sat)</sub> *3       | $I_C = 50A$ , $V_{GE} = 15V$ ,<br>$T_j = 25$ °C<br>$T_j = 175$ °C | -    | 1.65<br>2.2 | 2.1     | ٧    |
| Input Capacitance                         | C <sub>ies</sub>              | V <sub>CE</sub> = 30V,  | -    | 2770        | -       |      |
| Output Capacitance                        | C <sub>oes</sub>              | $V_{GE} = 0V$ ,   | -    | 106         | -       | pF   |
| Reverse transfer Capacitance              | $C_{res}$                     | f = 1MHz  | -    | 43          | -       |      |
| Total Gate Charge                         | $Q_g$                         | V <sub>CE</sub> = 300V,   | -    | 94          | -       |      |
| Gate - Emitter Charge                     | $Q_ge$                        | $I_{\rm C} = 50A$ ,   | -    | 22          | -       | nC   |
| Gate - Collector Charge                   | $Q_{gc}$                      | V <sub>GE</sub> = 15V   | -    | 31          | -       |      |

<sup>\*3</sup> Design assurance without measurement

# **●Chip Information**



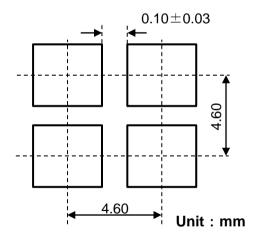
Unit: µm

Pad Area

1 : Gate Bonding Pad

2 : Emitter Bonding Pad

Backside: Collector



| Wafer Size  | 200mm  |
|---|--|
| Wafer Thickness   | 0.08±0.01mm  |
| Chip Size   | 4.60mm×4.60mm  |
| Cut Line Width  | 0.10±0.03mm  |
| Top Side Metallization  | AlCu:4.4µm   |
| Back Side Metallization   | Ti/Ni:0.4µm/Au:0.05µm  |
| Passivation   | Polyimide  |
| Chip Size Cut Line Width Top Side Metallization Back Side Metallization | 4.60mm×4.60mm<br>0.10±0.03mm<br>AlCu:4.4µm<br>Ti/Ni:0.4µm/Au:0.05µ |

# •Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

| This chip data sheet refers to the device data sheet | RGT00TS65D |
|--|------------|
|  |            |

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